

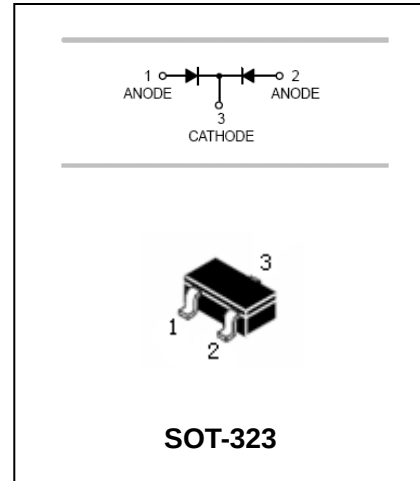
Dual Surface Mount Switching Diode

DAN202U-TR

FEATURES

- For types of packaging are available
- High speed switching
- Suitable for high packing density layout
- High reliability

HF



APPLICATIONS

- For general purpose switching applications

ORDERING INFORMATION

Type No.	Marking	Package Code
DAN202U-TR	N	SOT-323

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	V_{RM}	85	V
Diode reverse voltage	V_R	80	V
Forward continuous Current (peak)	I_F	300	mA
Average forward current	I_O	100	mA
Surge Current (t=1.0us)	I_{surge}	4	A
Power Dissipation	P_d	200	mW
Junction temperature	T_J	150	°C
Storage temperature range	T_{stg}	-65 to +150	°C

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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R = 100\mu A$	80	-	-	V
Reverse voltage leakage current	I_R	$V_R = 70V$	-	-	0.1	μA
Forward voltage	V_F	$I_F = 1mA$	-	0.60	-	V
		$I_F = 10mA$	-	0.72	-	V
		$I_F = 100mA$	-	0.92	1.2	V
Diode capacitance	C_D	$V_R = 6V$ $f = 1MHz$	-	0.9	3.5	pF
Reverse recovery time	t_{rr}	$V_R = 6V, I_F = 5mA$	-	1.8	4	ns

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

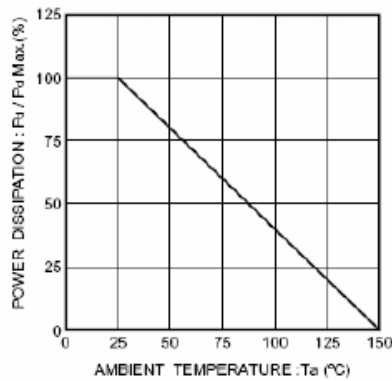


Fig.1 Power attenuation curve

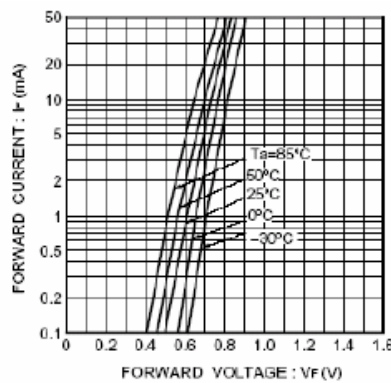


Fig.2 Forward characteristics (P Type)

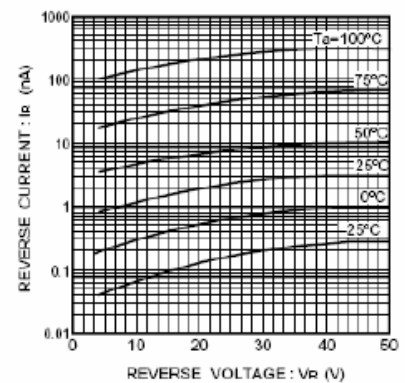


Fig.3 Reverse characteristics (P Type)

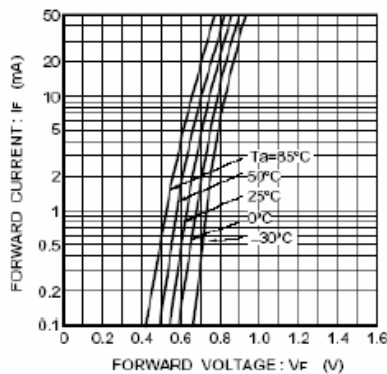


Fig.4 Forward characteristics (N Type)

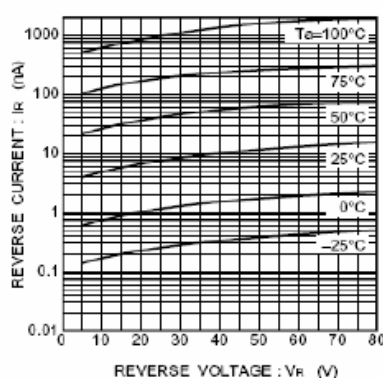


Fig.5 Reverse characteristics (N Type)

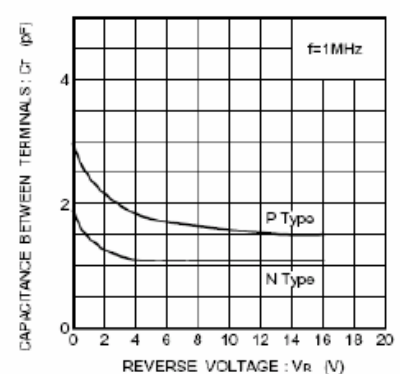


Fig.6 Capacitance between terminals characteristics

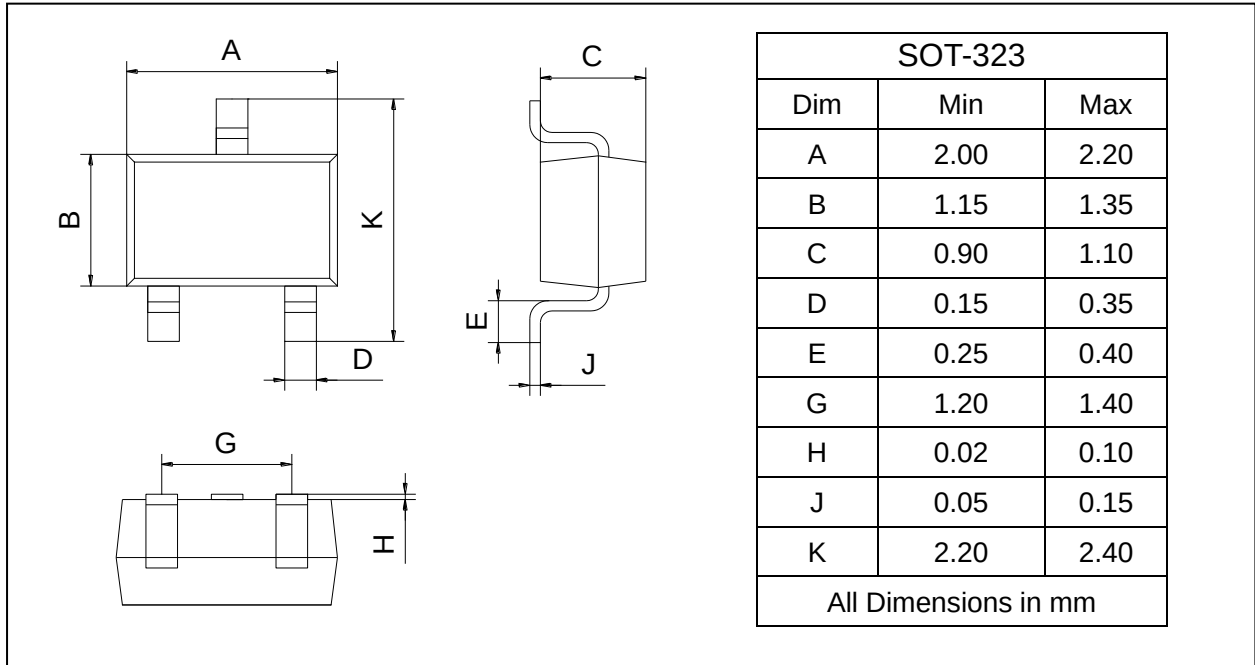
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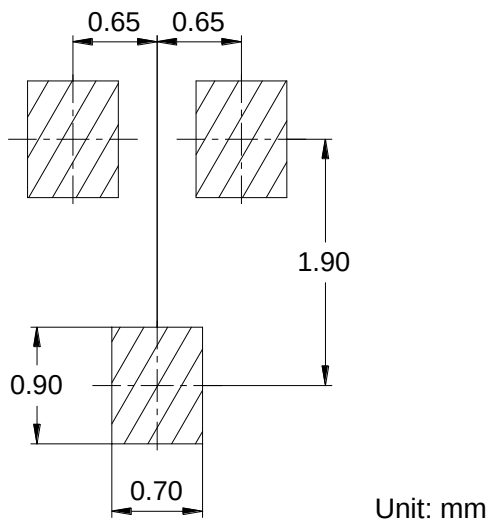
PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
DAN202U-TR	SOT-323	3000pcs / Tape & Reel